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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	668-BBGA Exposed Pad
Supplier Device Package	668-PBGA-PGE (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8358cvraddda

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	42	OV_{DD} = 3.3 V
PCI signals	25	
PCI output clocks (including PCI_SYNC_OUT)	42	
DDR signal	20 36 (half-strength mode)[1]	GV_{DD} = 2.5 V
DDR2 signal	18 36 (half-strength mode)[1]	GV_{DD} = 1.8 V
10/100/1000 Ethernet signals	42	LV_{DD} = 2.5/3.3 V
DUART, system control, I^2C, SPI, JTAG	42	OV_{DD} = 3.3 V
GPIO signals	42	OV_{DD} = 3.3 V LV_{DD} = 2.5/3.3 V

[1] DDR output impedance values for half strength mode are verified by design and not tested.

2.2 Power Sequencing

This section details the power sequencing considerations for the MPC8358E.

2.2.1 Power-Up Sequencing

MPC8358E does not require the core supply voltage (V_{DD} and AV_{DD}) and I/O supply voltages (GV_{DD}, LV_{DD}, and OV_{DD}) to be applied in any particular order. During the power ramp up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there may be a period of time that all input and output pins will actively be driven and cause contention and excessive current. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD}, LV_{DD}, and OV_{DD}) and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V, see Figure 4.

4.1 DC Electrical Characteristics

Table 6 provides the clock input (CLKIN/PCI_SYNC_IN) DC timing specifications for the device.

Table 6. CLKIN DC Electrical Characteristics

Parameter	Condition	Symbol	Min	Max	Unit
Input high voltage	—	V_{IH}	2.7	OV_{DD} + 0.3	V
Input low voltage	—	V_{IL}	–0.3	0.4	V
CLKIN input current	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	I_{IN}	—	±10	µA
PCI_SYNC_IN input current	$0 \text{ V} \leq V_{IN} \leq 0.5\text{V}$ or $OV_{DD} - 0.5\text{V} \leq V_{IN} \leq OV_{DD}$	I_{IN}	—	±10	µA
PCI_SYNC_IN input current	$0.5 \text{ V} \leq V_{IN} \leq OV_{DD} - 0.5 \text{ V}$	I_{IN}	—	±100	µA

4.2 AC Electrical Characteristics

The primary clock source for the device can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. Table 7 provides the clock input (CLKIN/PCI_CLK) AC timing specifications for the device.

Table 7. CLKIN AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
CLKIN/PCI_CLK frequency	f_{CLKIN}	—	—	66.67	MHz	1
CLKIN/PCI_CLK cycle time	t_{CLKIN}	15	—	—	ns	—
CLKIN/PCI_CLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	2.3	ns	2
CLKIN/PCI_CLK duty cycle	t_{KHK}/t_{CLKIN}	40	—	60	%	3
CLKIN/PCI_CLK jitter	—	—	—	±150	ps	4, 5

Notes:

1. **Caution:** The system, core, USB, security, and 10/100/1000 Ethernet must not exceed their respective maximum or minimum operating frequencies.
2. Rise and fall times for CLKIN/PCI_CLK are measured at 0.4 V and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the total input jitter—short term and long term—and is guaranteed by design.
5. The CLKIN/PCI_CLK driver's closed loop jitter bandwidth should be <500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track CLKIN drivers with the specified jitter.

Table 9. RESET Pins DC Electrical Characteristics (continued)

Characteristic	Symbol	Condition	Min	Max	Unit
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Notes:

1. This table applies for pins $\overline{\text{PORESET}}$, $\overline{\text{HRESET}}$, $\overline{\text{SRESET}}$, and $\overline{\text{QUIESCE}}$.
2. $\overline{\text{HRESET}}$ and $\overline{\text{SRESET}}$ are open drain pins, thus V_{OH} is not relevant for those pins.

5.2 RESET AC Electrical Characteristics

This section describes the AC electrical specifications for the reset initialization timing requirements of the device. Table 10 provides the reset initialization AC timing specifications for the DDR SDRAM component(s).

Table 10. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$ or $\overline{\text{SRESET}}$ (input) to activate reset flow	32	—	$t_{\text{PCI\_SYNC\_IN}}$	1
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to CLKIN when the device is in PCI host mode	32	—	t_{CLKIN}	2
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to PCI_SYNC_IN when the device is in PCI agent mode	32	—	$t_{\text{PCI\_SYNC\_IN}}$	1
$\overline{\text{HRESET}}$/$\overline{\text{SRESET}}$ assertion (output)	512	—	$t_{\text{PCI\_SYNC\_IN}}$	1
$\overline{\text{HRESET}}$ negation to $\overline{\text{SRESET}}$ negation (output)	16	—	$t_{\text{PCI\_SYNC\_IN}}$	1
Input setup time for POR config signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of $\overline{\text{PORESET}}$ when the device is in PCI host mode	4	—	t_{CLKIN}	2
Input setup time for POR config signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of $\overline{\text{PORESET}}$ when the device is in PCI agent mode	4	—	$t_{\text{PCI\_SYNC\_IN}}$	1
Input hold time for POR config signals with respect to negation of $\overline{\text{HRESET}}$	0	—	ns	
Time for the device to turn off POR config signals with respect to the assertion of $\overline{\text{HRESET}}$	—	4	ns	3
Time for the device to turn on POR config signals with respect to the negation of $\overline{\text{HRESET}}$	1	—	$t_{\text{PCI\_SYNC\_IN}}$	1, 3

Notes:

1. $t_{\text{PCI\_SYNC\_IN}}$ is the clock period of the input clock applied to PCI_SYNC_IN. When the device is In PCI host mode the primary clock is applied to the CLKIN input, and PCI_SYNC_IN period depends on the value of CFG_CLKIN_DIV. See the *MPC8360E PowerQUICC II Pro Integrated Communications Processor Family Reference Manual* for more details.
2. t_{CLKIN} is the clock period of the input clock applied to CLKIN. It is only valid when the device is in PCI host mode. See the *MPC8360E PowerQUICC II Pro Integrated Communications Processor Family Reference Manual* for more details.
3. POR config signals consists of CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV.

Table 16 provides the DDR capacitance when GV_{DD}(typ) = 2.5 V.

Table 16. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

6.2 DDR and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR and DDR2 SDRAM interface.

6.2.1 DDR and DDR2 SDRAM Input AC Timing Specifications

Table 17 provides the input AC timing specifications for the DDR2 SDRAM interface when GV_{DD}(typ) = 1.8 V.

Table 17. DDR2 SDRAM Input AC Timing Specifications for GV_{DD}(typ) = 1.8 V

At recommended operating conditions with GV_{DD} of 1.8 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V	—

Table 18 provides the input AC timing specifications for the DDR SDRAM interface when GV_{DD}(typ) = 2.5 V.

Table 18. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.31	—	V	—

Note:

1. Maximum possible skew between a data strobe (MDQS[n]) and any corresponding bit of data (MDQ[8n + {0...7}] if 0 ≤ n ≤ 7) or ECC (MECC[{0...7}] if n = 8).

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications for Source Synchronous Mode (continued)

At recommended operating conditions with GV_{DD} of (1.8 V or 2.5 V) ± 5%.

Parameter[8]	Symbol[1]	Min	Max	Unit	Notes
ADDR/CMD output setup with respect to MCK 266 MHz 200 MHz	t_{DDKHAS}	 2.8 3.5	—	ns	4
ADDR/CMD output hold with respect to MCK 266 MHz—DDR1 266 MHz—DDR2 200 MHz	t_{DDKHAX}	 2.6 2.8 3.5	—	ns	4
$\overline{\text{MCS}}$(n) output setup with respect to MCK 266 MHz 200 MHz	t_{DDKHCS}	 2.8 3.5	—	ns	4
$\overline{\text{MCS}}$(n) output hold with respect to MCK 266 MHz 200 MHz	t_{DDKHCX}	 2.7 3.5	—	ns	4
MCK to MDQS	t_{DDKHMH}	–0.75	0.6	ns	5
MDQ/MECC/MDM output setup with respect to MDQS 266 MHz 200 MHz	t_{DDKHDS}, t_{DDKLDS}	 1.0 1.2	—	ns	6
MDQ/MECC/MDM output hold with respect to MDQS 266 MHz 200 MHz	t_{DDKHDX}, t_{DDKLDX}	 1.0 1.2	—	ns	6
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	7

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications for Source Synchronous Mode (continued)

At recommended operating conditions with GV_{DD} of (1.8 V or 2.5 V) ± 5%.

Parameter[8]	Symbol[1]	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKHME}	–0.6	0.9	ns	7

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. In the source synchronous mode, MCK/$\overline{\text{MCK}}$ can be shifted in ¼ applied cycle increments through the clock control register. For the skew measurements referenced for t_{AOSKEW} it is assumed that the clock adjustment is set to align the address/command valid with the rising edge of MCK.
4. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by ½ applied cycle.
5. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. In source synchronous mode, this will typically be set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters have been set to the same adjustment value. See the *MPC8360E PowerQUICC II Pro Integrated Communications Processor Family Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
6. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the device.
7. All outputs are referenced to the rising edge of MCK(n) at the pins of the device. Note that t_{DDKHMP} follows the symbol conventions described in note 1.
8. AC timing values are based on the DDR data rate, which is twice the DDR memory bus frequency.

Figure 6 shows the DDR SDRAM output timing for address skew with respect to any MCK.

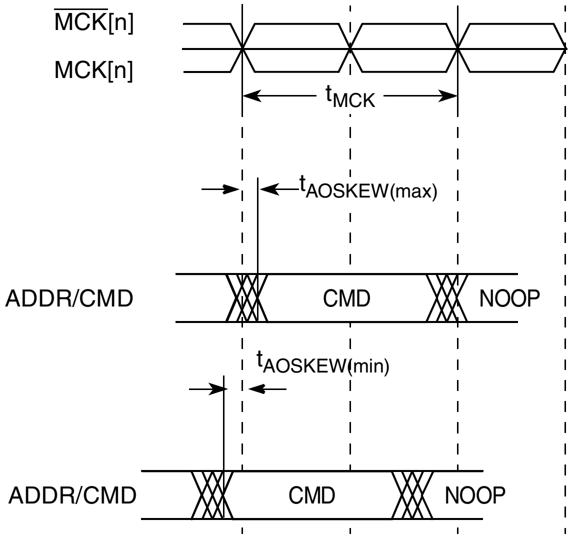


Figure 6. Timing Diagram for t_{AOSKEW} Measurement

Figure 13 shows the MII receive AC timing diagram.

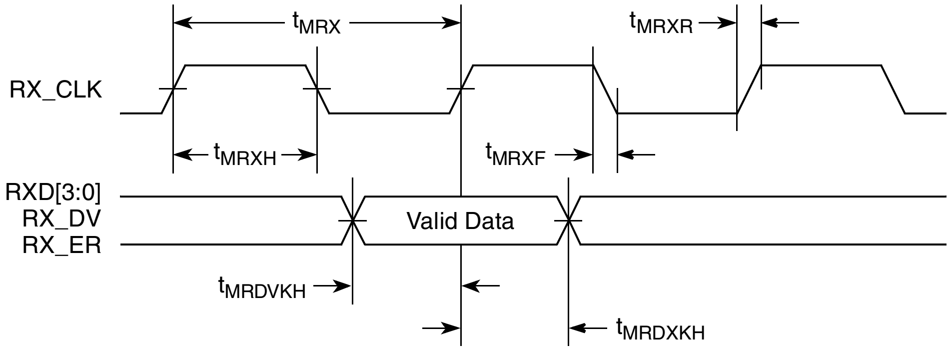


Figure 13. MII Receive AC Timing Diagram

8.2.3 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

8.2.3.1 RMII Transmit AC Timing Specifications

Table 30 provides the RMII transmit AC timing specifications.

Table 30. RMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
REF_CLK clock	t_{RMX}	—	20	—	ns
REF_CLK duty cycle	t_{RMXH}/t_{RMX}	35	—	65	%
REF_CLK to RMII data TXD[1:0], TX_EN delay	$t_{RMTKHDX}$ $t_{RMTKHDV}$	2 —	—	— 10	ns
REF_CLK data clock rise time	t_{RMXR}	1.0	—	4.0	ns
REF_CLK data clock fall time	t_{RMXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first three letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{RMTKHDX}$ symbolizes RMII transmit timing (RMT) for the time t_{RMX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII(RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Table 36. MII Management AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD} is 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
MDC fall time	t_{MDHF}	—	—	10	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, $t_{MDRDVKH}$ symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the csb_clk speed (that is, for a csb_clk of 267 MHz, the maximum frequency is 8.3 MHz and the minimum frequency is 1.2 MHz; for a csb_clk of 375 MHz, the maximum frequency is 11.7 MHz and the minimum frequency is 1.7 MHz).
3. This parameter is dependent on the ce_clk speed (that is, for a ce_clk of 200 MHz, the delay is 90 ns and for a ce_clk of 300 MHz, the delay is 63 ns).

Figure 20 shows the MII management AC timing diagram.

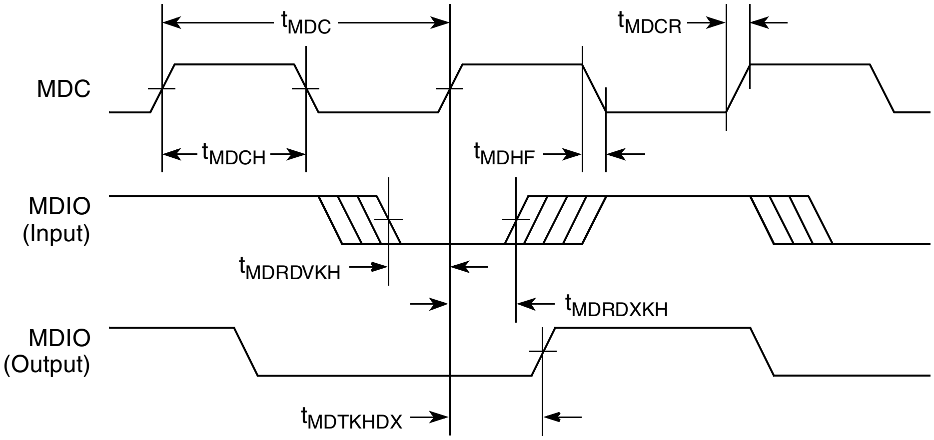


Figure 20. MII Management Interface Timing Diagram

8.3.3 IEEE 1588 Timer AC Specifications

Table 37 provides the IEEE 1588 timer AC specifications.

Table 37. IEEE 1588 Timer AC Specifications

Parameter	Symbol	Min	Max	Unit	Notes
Timer clock frequency	t_{TMRCK}	0	70	MHz	1
Input setup to timer clock	t_{TMRCKS}	—	—	—	2, 3
Input hold from timer clock	t_{TMRCKH}	—	—	—	2, 3
Output clock to output valid	t_{GCLKNV}	0	6	ns	—

Table 37. IEEE 1588 Timer AC Specifications (continued)

Parameter	Symbol	Min	Max	Unit	Notes
Timer alarm to output valid	t_{TMRAL}	—	—	—	2

Notes:
1. The timer can operate on rtc_clock or tmr_clock. These clocks get muxed and any one of them can be selected. The minimum and maximum requirement for both rtc_clock and tmr_clock are the same.
2. These are asynchronous signals.
3. Inputs need to be stable at least one TMR clock.

9 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8358E.

9.1 Local Bus DC Electrical Characteristics

Table 38 provides the DC electrical characteristics for the local bus interface.

Table 38. Local Bus DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 µA	V_{OH}	OV_{DD} – 0.4	—	V
Low-level output voltage, I_{OL} = 100 µA	V_{OL}	—	0.2	V
Input current	I_{IN}	—	±10	µA

9.2 Local Bus AC Electrical Specifications

Table 39 describes the general timing parameters of the local bus interface of the device.

Table 39. Local Bus General Timing Parameters—DLL Enabled

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	—	ns	2
Input setup to local bus clock (except LUPWAIT)	$t_{LBIVKH1}$	1.7	—	ns	3, 4
LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.9	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3.0	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7

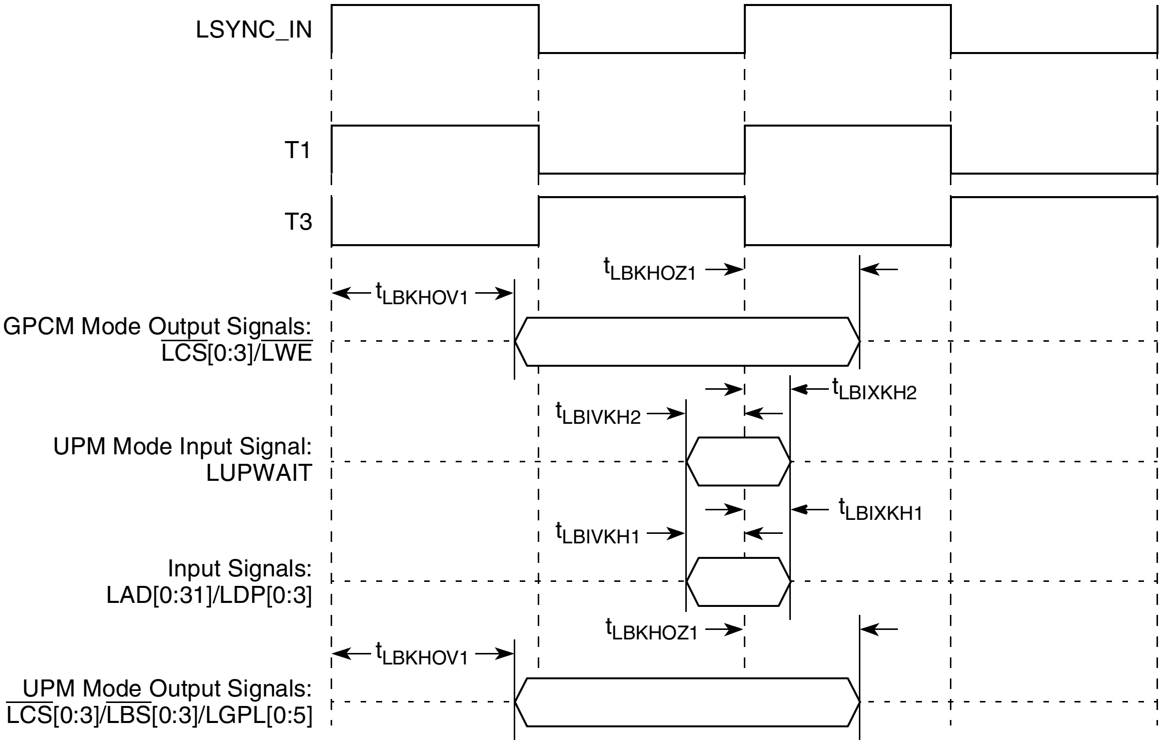


Figure 24. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (DLL Enabled)

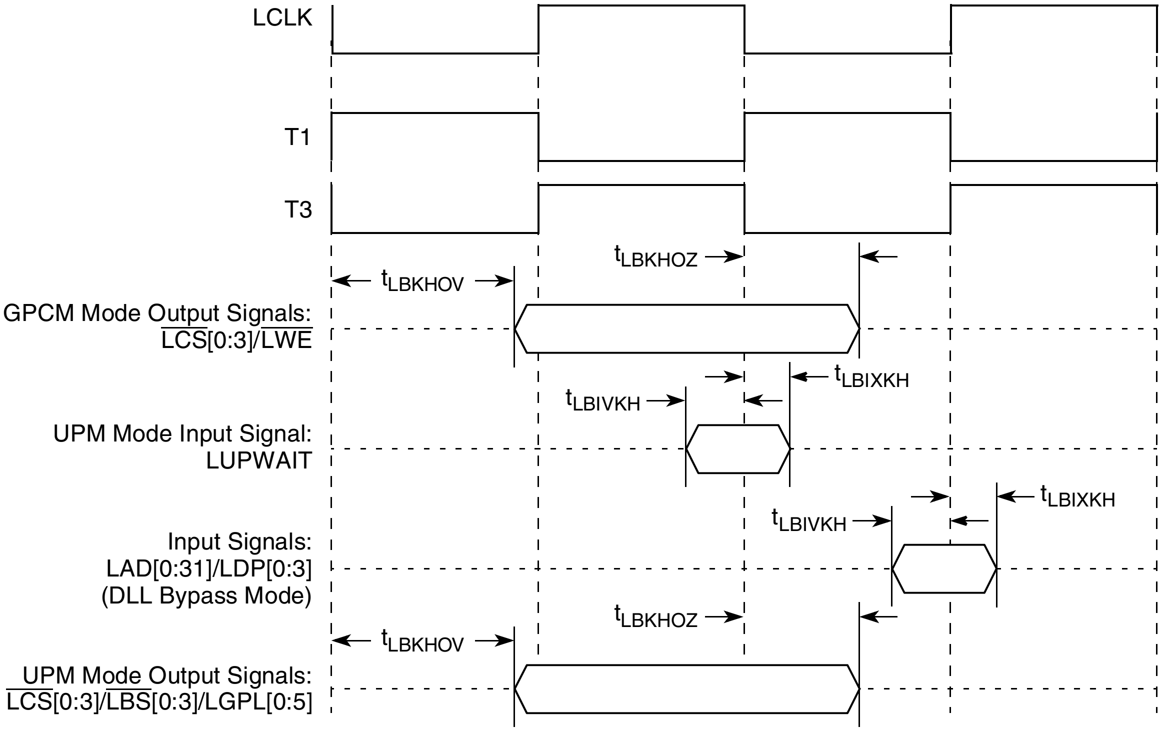


Figure 25. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (DLL Bypass Mode)

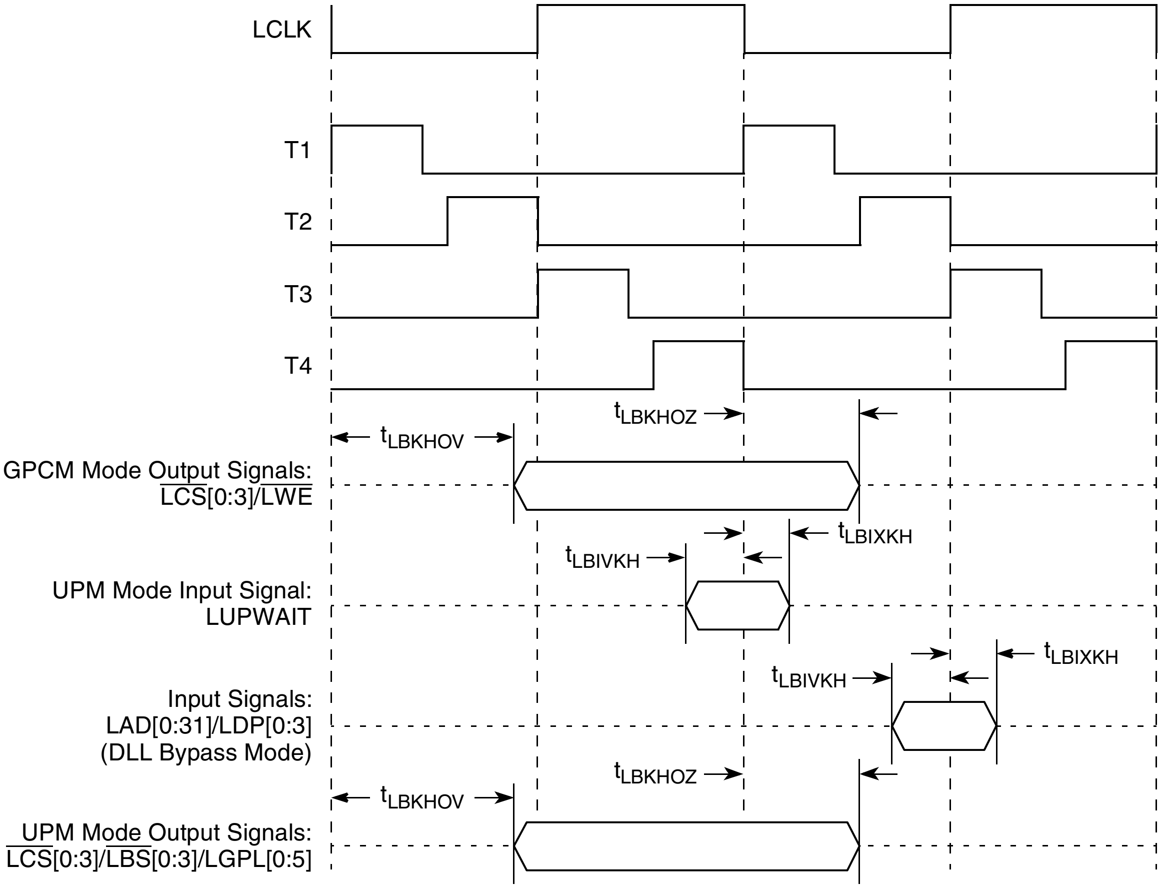


Figure 26. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4 (DLL Bypass Mode)

16.1 SPI DC Electrical Characteristics

Table 54 provides the DC electrical characteristics for the device SPI.

Table 54. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = –6.0$ mA	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 6.0$ mA	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2$ mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 \text{ V} \le V_{IN} \le OV_{DD}$	—	±10	μA

16.2 SPI AC Timing Specifications

Table 55 and provide the SPI input and output AC timing specifications.

Table 55. SPI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
SPI outputs—Master mode (internal clock) delay	t_{NIKHOX} t_{NIKHOV}	0.4 —	— 8	ns
SPI outputs—Slave mode (external clock) delay	t_{NEKHOX} t_{NEKHOV}	2 —	— 8	ns
SPI inputs—Master mode (internal clock) input setup time	t_{NIIVKH}	8	—	ns
SPI inputs—Master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).

Figure 40 provides the AC test load for the SPI.

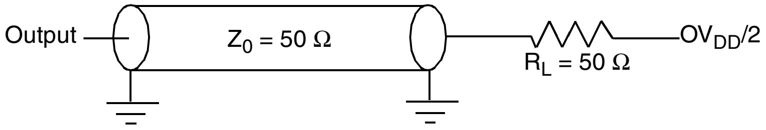
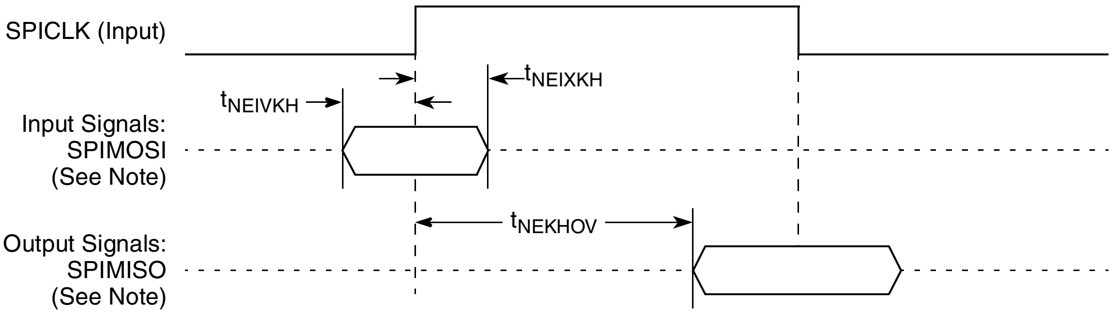


Figure 40. SPI AC Test Load

Figure 41 and Figure 42 represent the AC timing from Table 55. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

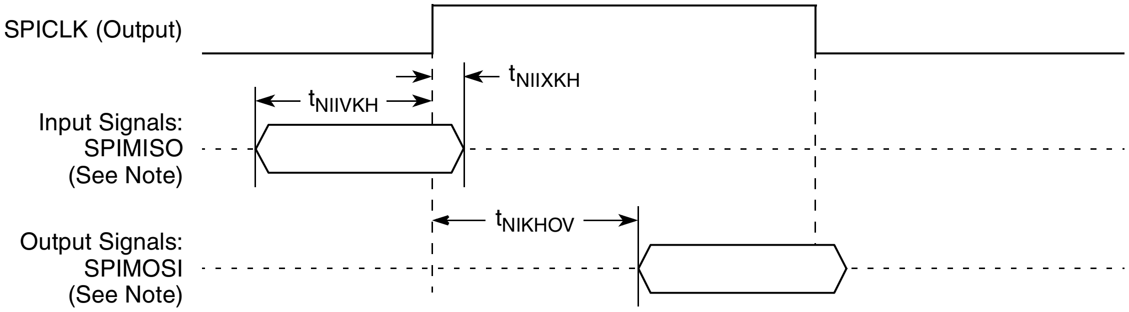
Figure 41 shows the SPI timing in slave mode (external clock).



Note: The clock edge is selectable on SPI.

Figure 41. SPI AC Timing in Slave Mode (External Clock) Diagram

Figure 42 shows the SPI timing in Master mode (internal clock).



Note: The clock edge is selectable on SPI.

Figure 42. SPI AC Timing in Master Mode (Internal Clock) Diagram

17 TDM/SI

This section describes the DC and AC electrical specifications for the time-division-multiplexed and serial interface of the MPC8358E.

17.1 TDM/SI DC Electrical Characteristics

Table 56 provides the DC electrical characteristics for the device TDM/SI.

Table 56. TDM/SI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = -2.0$ mA	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 3.2$ mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V

Table 56. TDM/SI DC Electrical Characteristics (continued)

Characteristic	Symbol	Condition	Min	Max	Unit
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤ V_{IN} ≤ OV_{DD}	—	±10	μA

17.2 TDM/SI AC Timing Specifications

Table 57 provides the TDM/SI input and output AC timing specifications.

Table 57. TDM/SI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max[3]	Unit
TDM/SI outputs—External clock delay	t_{SEKHOV}	2	10	ns
TDM/SI outputs—External clock high impedance	t_{SEKHOX}	2	10	ns
TDM/SI inputs—External clock input setup time	t_{SEIVKH}	5	—	ns
TDM/SI inputs—External clock input hold time	t_{SEIXKH}	2	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{SEKHOX} symbolizes the TDM/SI outputs external timing (SE) for the time $t_{TDM/SI}$ memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).
3. Timings are measured from the positive or negative edge of the clock, according to SIxMR [CE] and SITXCEI[TXCEIx]. See the *MPC8360E Integrated Communications Processor Family Reference Manual* for more details.

Figure 43 provides the AC test load for the TDM/SI.

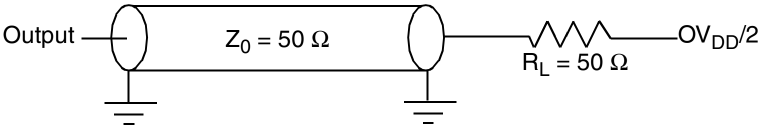


Figure 43. TDM/SI AC Test Load

Figure 44 represents the AC timing from Table 55. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

Figure 48 provides the AC test load.

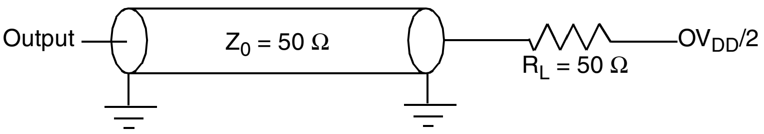
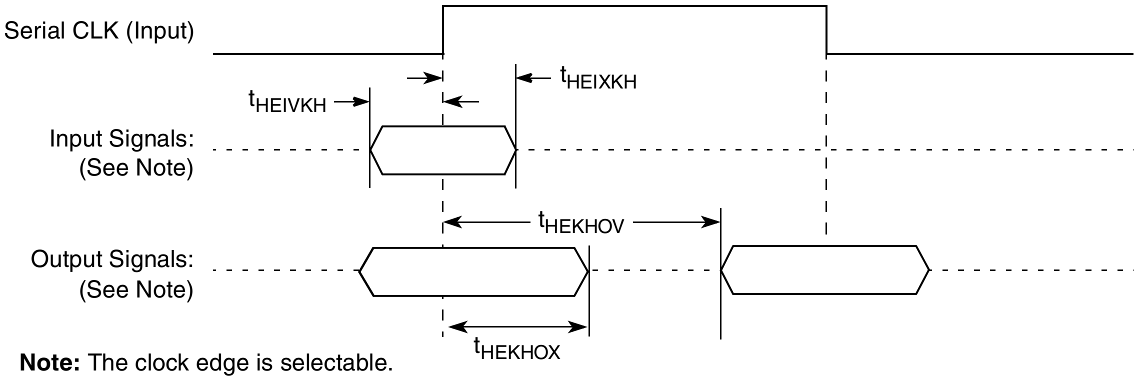


Figure 48. AC Test Load

19.3 AC Test Load

Figure 49 and Figure 50 represent the AC timing from Table 61 and Table 62. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

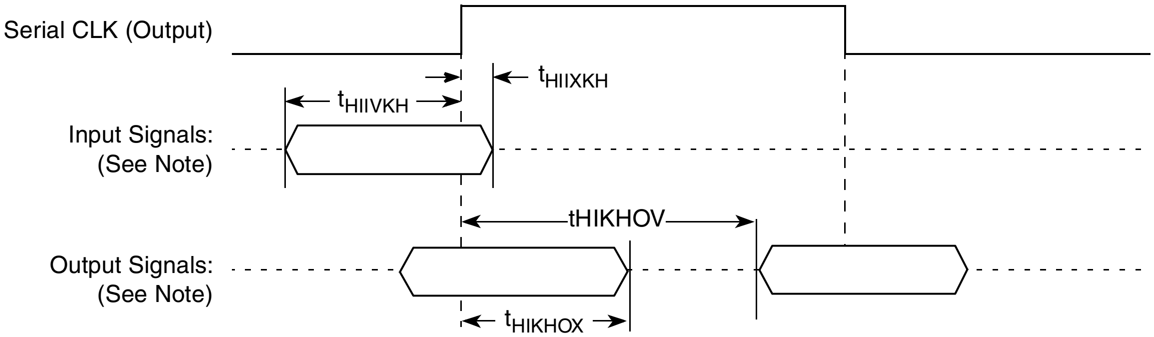
Figure 49 shows the timing with external clock.



Note: The clock edge is selectable.

Figure 49. AC Timing (External Clock) Diagram

Figure 50 shows the timing with internal clock.



Note: The clock edge is selectable.

Figure 50. AC Timing (Internal Clock) Diagram

20 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8358E.

20.1 USB DC Electrical Characteristics

Table 63 provides the DC electrical characteristics for the USB interface.

Table 63. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 µA	V_{OH}	OV_{DD} – 0.4	—	V
Low-level output voltage, I_{OL} = 100 µA	V_{OL}	—	0.2	V
Input current	I_{IN}	—	±10	µA

20.2 USB AC Electrical Specifications

Table 64 describes the general timing parameters of the USB interface of the device.

Table 64. USB General Timing Parameters

Parameter	Symbol[1]	Min	Max	Unit	Notes
USB clock cycle time	t_{USCK}	20.83	—	ns	Full speed 48 MHz
USB clock cycle time	t_{USCK}	166.67	—	ns	Low speed 6 MHz
Skew between TXP and TXN	t_{USTSPN}	—	5	ns	—
Skew among RXP, RXN, and RXD	$t_{USRSPND}$	—	10	ns	Full speed transitions
Skew among RXP, RXN, and RXD	t_{USRPND}	—	100	ns	Low speed transitions

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(state)(signal)}}$ for receive signals and $t_{\text{(first two letters of functional block)(state)(signal)}}$ for transmit signals. For example, $t_{USRSPND}$ symbolizes USB timing (US) for the USB receive signals skew (RS) among RXP, RXN, and RXD (PND). Also, t_{USTSPN} symbolizes USB timing (US) for the USB transmit signals skew (TS) between TXP and TXN (PN).
2. Skew measurements are done at $OV_{DD}/2$ of the rising or falling edge of the signals.

Figure 51 provide the AC test load for the USB.

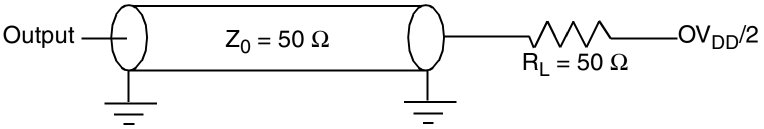


Figure 51. USB AC Test Load

4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
5. Parallelism measurement must exclude any effect of mark on top surface of package.
6. Distance from the seating plane to the encapsulant material.

21.3 Pinout Listings

Refer to AN3097, “MPC8360/MPC8358E PowerQUICC Design Checklist,” for proper pin termination and usage.

Table 65 shows the pin list of the MPC8358E PBGA package.

Table 65. MPC8358E PBGA Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
DDR SDRAM Memory Controller Interface				
MEMC_MDQ[0:63]	AD20, AG24, AF24, AH24, AF23, AE22, AH26, AD21, AH25, AD22, AF27, AB24, AG25, AC22, AE25, AC24, AD25, AB25, AC25, AG28, AD26, AE23, AG26, AC26, AD27, V25, AA28, AA25, Y26, W27, U24, W24, E28, H24, E26, D25, G27, H25, G26, F26, F27, F25, D26, F24, G25, E27, D27, C28, C27, F22, B26, F21, B28, E22, D24, C24, A25, E20, F20, D20, A23, C21, C23, E19	I/O	GV_{DD}	—
MEMC_MECC[0:7]	N26, N24, J26, H28, N28, P24, L26, K24	I/O	GV_{DD}	—
MEMC_MDM[0:8]	AG23, AD23, AE26, V28, G28, D28, D23, B24, U27	O	GV_{DD}	—
MEMC_MDQS[0:8]	AH23, AH27, AF28, T28, H26, E25, B25, A24, R28	I/O	GV_{DD}	—
MEMC_MBA[0:2]	V26, W28, Y28	O	GV_{DD}	—
MEMC_MA[0:14]	L25, M25, M24, K28, P28, T24, M27, R25, P25, L28, U26, M28, L27, K27, H27	O	GV_{DD}	—
MEMC_MODT[0:3]	AE21, AC19, E23, B23	—	GV_{DD}	6
$\overline{\text{MEMC\_MWE}}$	R27	O	GV_{DD}	—
$\overline{\text{MEMC\_MRAS}}$	W25	O	GV_{DD}	—
$\overline{\text{MEMC\_MCAS}}$	R24	O	GV_{DD}	—
$\overline{\text{MEMC\_MCS}}$[0:3]	T26, U28, J25, F28	O	GV_{DD}	—
MEMC_MCKE[0:1]	AD24, AE28	O	GV_{DD}	—
MEMC_MCK[0:5]	AG22, AG27, A26, C26, P26, E21	O	GV_{DD}	—
$\overline{\text{MEMC\_MCK}}$[0:5]	AF22, AF26, A27, B27, N27, D22	O	GV_{DD}	—
MDIC[0:1]	F19, AA27	I/O	GV_{DD}	11
PCI				
$\overline{\text{PCI\_INTA}}$/ PF[5]	R3	I/O	$LV_{DD}2$	2
$\overline{\text{PCI\_RESET\_OUT}}$/ PF[6]	P6	I/O	$LV_{DD}2$	—
PCI_AD[0:31]/ PG[0:31]	AB5, AC5, AG1, AA5, AF2, AD4, Y6, AF1, AE2, AC4, AD3, AE1, Y4, AC3, AD2, AD1, AB2, Y3, AA1, Y1, W1, V6, W3, V4, T5, W2, V5, V1, U4, V2, U2, T2	I/O	$LV_{DD}2$	—
$\overline{\text{PCI\_C\_BE}}$[0:3]/ PF[7:10]	Y5, AC2, Y2, U5	I/O	OV_{DD}	—

22.1 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] and RCWL[SVCOD] parameters. Table 68 shows the multiplication factor encodings for the system PLL.

Table 68. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	× 16
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111	× 7
1000	× 8
1001	× 9
1010	× 10
1011	× 11
1100	× 12
1101	× 13
1110	× 14
1111	× 15

The RCWL[SVCOD] denotes the system PLL VCO internal frequency as shown in Table 69.

Table 69. System PLL VCO Divider

RCWL[SVCOD]	VCO Divider
00	4
01	8
10	2
11	Reserved

NOTE

The VCO divider must be set properly so that the system VCO frequency is in the range of 600–1400 MHz.

22.4 Suggested PLL Configurations

To simplify the PLL configurations, the device might be separated into two clock domains. The first domain contains the CSB PLL and the core PLL. The core PLL is connected serially to the CSB PLL, and has the csb_clk as its input clock. The second clock domain has the QUICC Engine block PLL. The clock domains are independent, and each of their PLLs are configured separately. Both of the domains has one common input clock. Table 74 shows suggested PLL configurations for 33 and 66 MHz input clocks and illustrates each of the clock domains separately. Any combination of clock domains setting with same input clock are valid. Refer to Section 22, “Clocking,” for the appropriate operating frequencies for your device.

Table 74. Suggested PLL Configurations

Conf No.[1]	SPMF	CORE PLL	CEPMF	CEPDF	Input Clock Freq (MHz)	CSB Freq (MHz)	Core Freq (MHz)	QUICC Engine Freq (MHz)	400 (MHz)	533 (MHz)	667 (MHz)
33 MHz CLKIN/PCI_SYNC_IN Options											
s1	**0100**	**0000100**	æ	æ	33	133	266	—	∞	∞	∞
s2	**0100**	**0000101**	æ	æ	33	133	333	—	∞	∞	∞
s3	**0101**	**0000100**	æ	æ	33	166	333	—	∞	∞	∞
s4	**0101**	**0000101**	æ	æ	33	166	416	—	—	∞	∞
s5	**0110**	**0000100**	æ	æ	33	200	400	—	∞	∞	∞
s6	**0110**	**0000110**	æ	æ	33	200	600	—	—	—	∞
s7	**0111**	**0000011**	æ	æ	33	233	350	—	∞	∞	∞
s8	**0111**	**0000100**	æ	æ	33	233	466	—	—	∞	∞
s9	**0111**	**0000101**	æ	æ	33	233	583	—	—	—	∞
s10	**1000**	**0000011**	æ	æ	33	266	400	—	∞	∞	∞
s11	**1000**	**0000100**	æ	æ	33	266	533	—	—	∞	∞
s12	**1000**	**0000101**	æ	æ	33	266	667	—	—	—	∞
s13	**1001**	**0000010**	æ	æ	33	300	300	—	∞	∞	∞
s14	**1001**	**0000011**	æ	æ	33	300	450	—	—	∞	∞
s15	**1001**	**0000100**	æ	æ	33	300	600	—	—	—	∞
s16	**1010**	**0000010**	æ	æ	33	333	333	—	∞	∞	∞
s17	**1010**	**0000011**	æ	æ	33	333	500	—	—	∞	∞
s18	**1010**	**0000100**	æ	æ	33	333	667	—	—	—	∞
c1	æ	æ	**01001**	**0**	33	—	—	300	∞	∞	∞
c2	æ	æ	**01100**	**0**	33	—	—	400	∞	∞	∞
c3	æ	æ	**01110**	**0**	33	—	—	466	—	∞	∞
c4	æ	æ	**01111**	**0**	33	—	—	500	—	∞	∞

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Document Number: MPC8358EEC
Rev. 3
01/2011